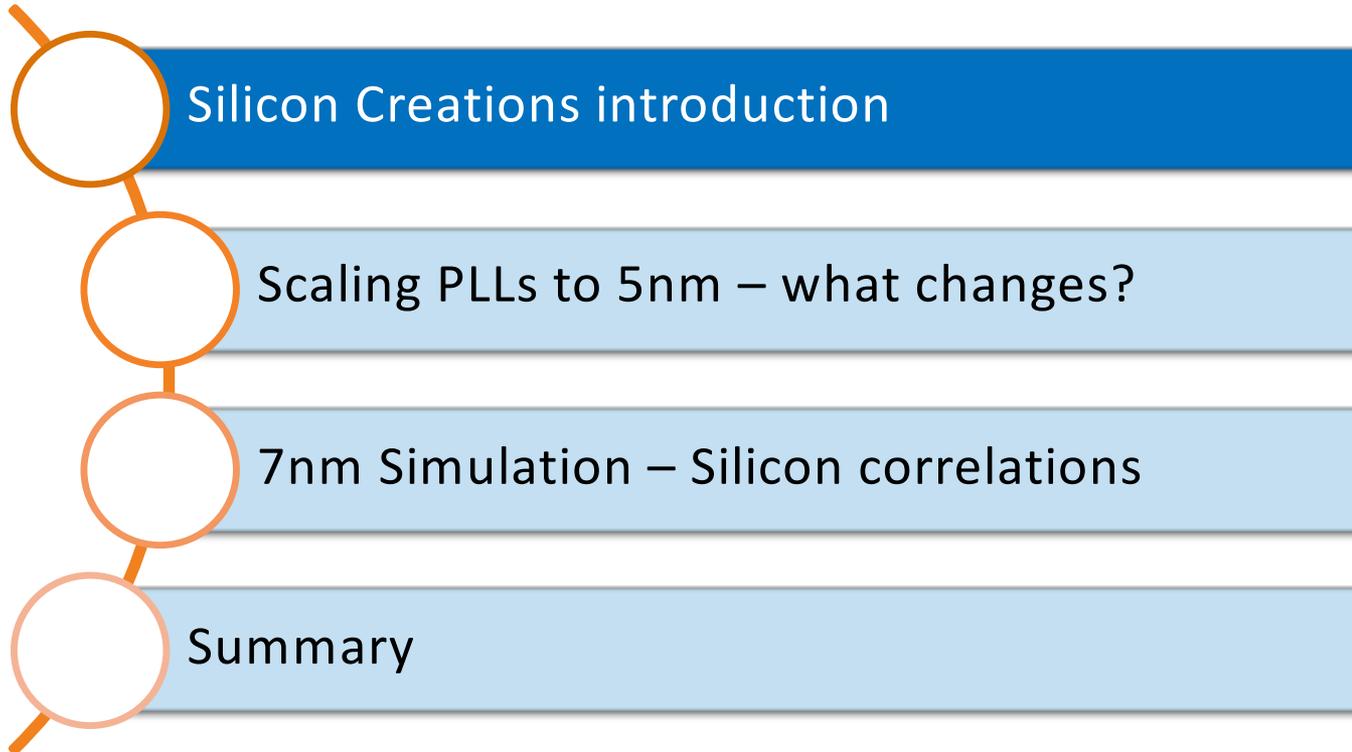
A horizontal strip of a blue-tinted image showing a close-up of a microchip or integrated circuit, with various components and patterns visible.

High Performance PLL Design in TSMC 5nm FinFET Process

Randy Caplan

Executive Vice President & Co-Founder, Silicon Creations

June 25, 2018



Silicon Creations Overview



- IP provider of PLLs, Oscillators and High-speed Interface
- Founded 2006 – self-funded, profitable and growing
- Design offices in Atlanta and Krakow, Poland
- High quality development, award winning support
- >160 customers (>60 in China)
- Mass production from 7nm to >180nm, 5nm coming soon



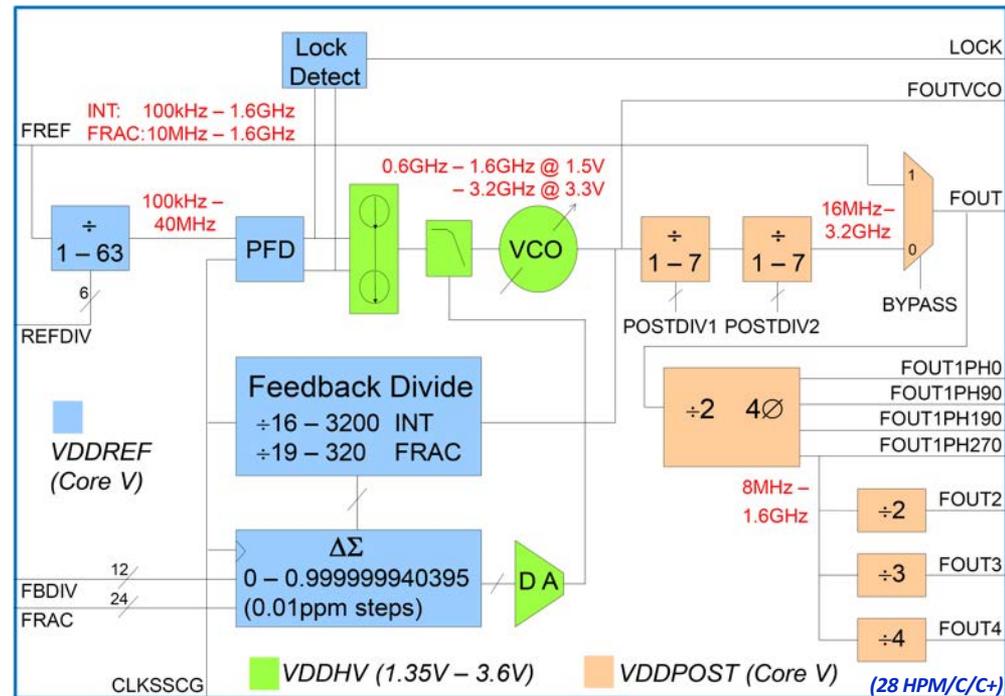
Awards for quality & support

- 2017
 - Audience choice paper, USA OIP
 - Mixed-Signal IP Partner of the year
- 2014
 - Best Emerging IP vendor



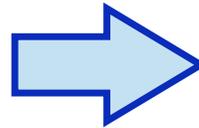
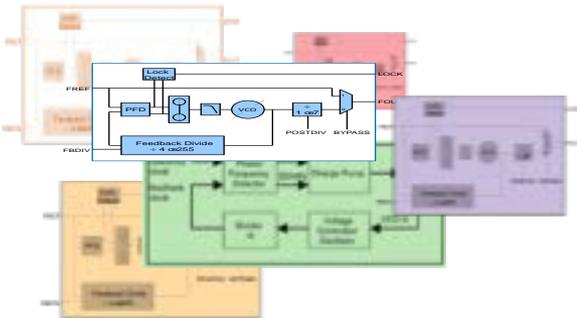
Fractional Ring PLL

- “One-Size-Fits-All” Synthesizer: flexibility reduces risk
 - Any crystal; <0.01ppm frequency step
- Programmable Power – Jitter Optimization
 - < 1mW
 - Long Term Jitter < 5ps RMS
- Production from 7nm, 5nm in development
- Derivative PLLs for
 - Core voltage only
 - Integer-only
 - Low area
 - Ultra-low jitter
 - Ultra-low power

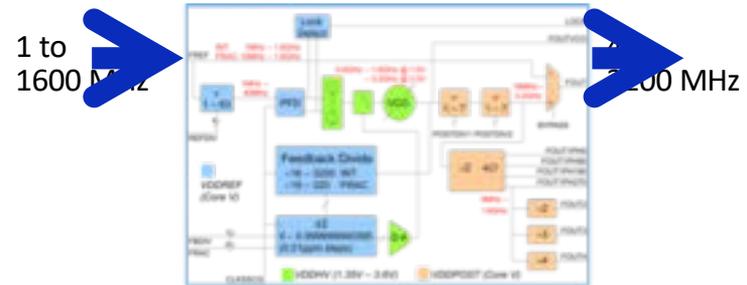


Why our Fractional PLL?

Competitors



Silicon Creations



Risky & expensive

- Built new each time
- Narrow input/output ranges
... need new masks to adjust
- Buy a new IP for every clock

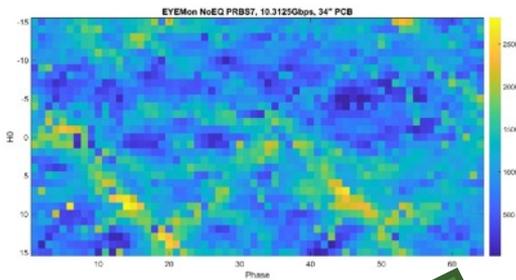


Lower risk & lower cost

- Predictable, measured
- Wide range, programmable
power-performance tradeoffs
- One PLL, many applications – save \$, ¥, €
- Best support

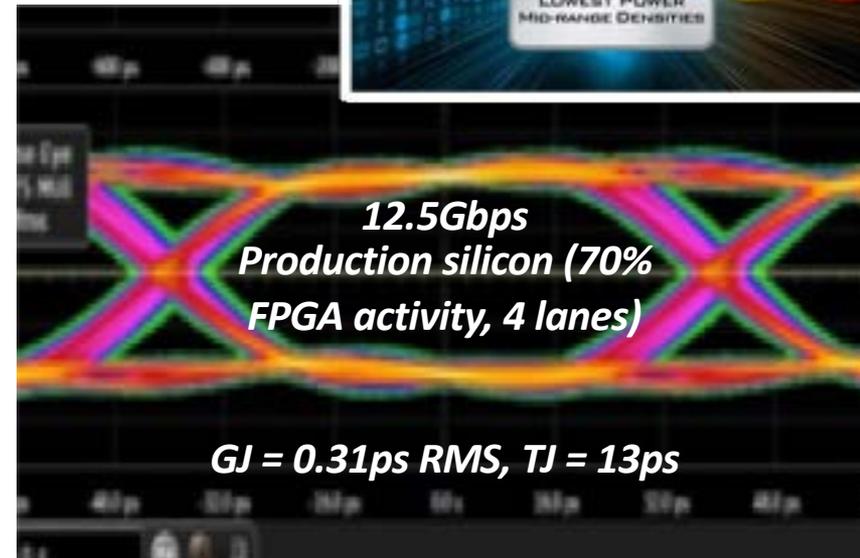
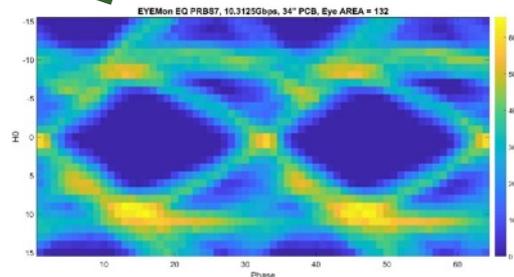
Multi-Protocol SerDes PMA

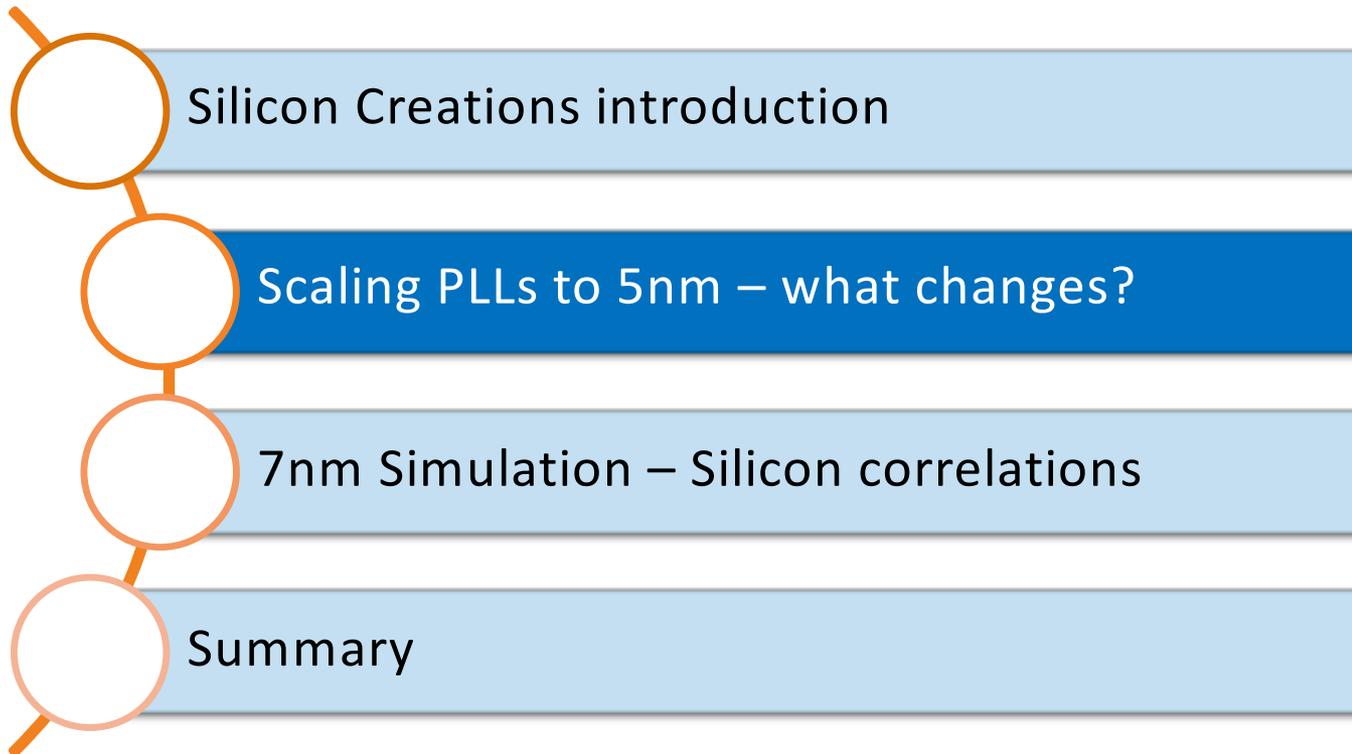
- 0.25 – 16Gbps SerDes PMA (28LP, 40 LP, 12/16FFC soon)
- Low Power (mW/Gbps/lane): SR <4.5mW, LR <8.6mW
- Jitter cleaner Tx Ring PLL → Low Area



(10.3Gbps,
25dB channel
loss)

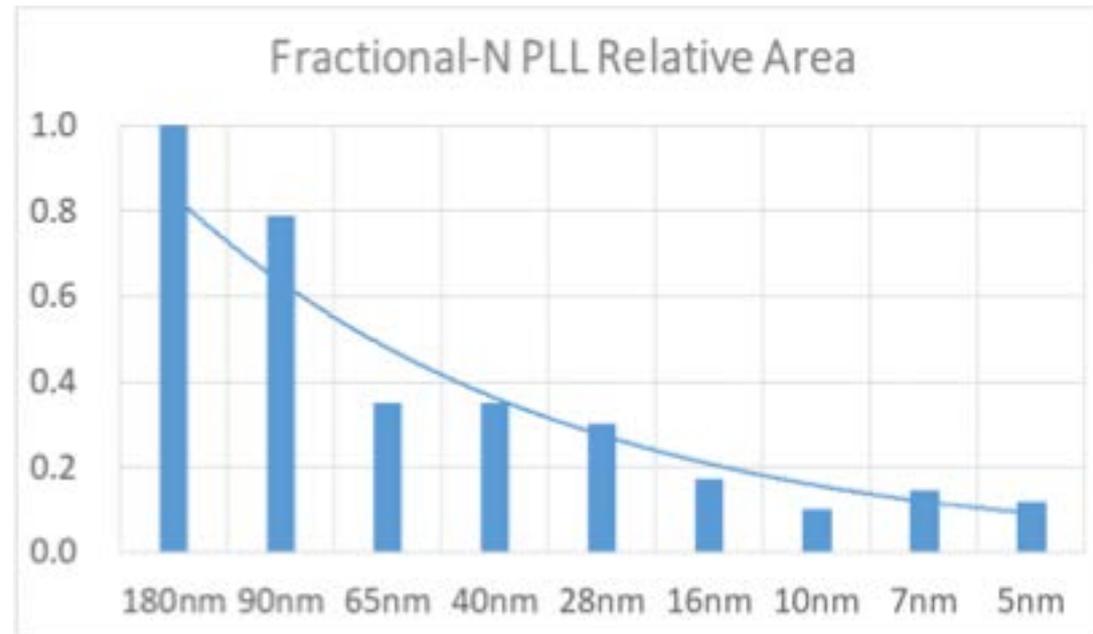
5-tap DFE + CTLE
+ Eye monitor +
Adaptive Eq.
→ >30 protocols





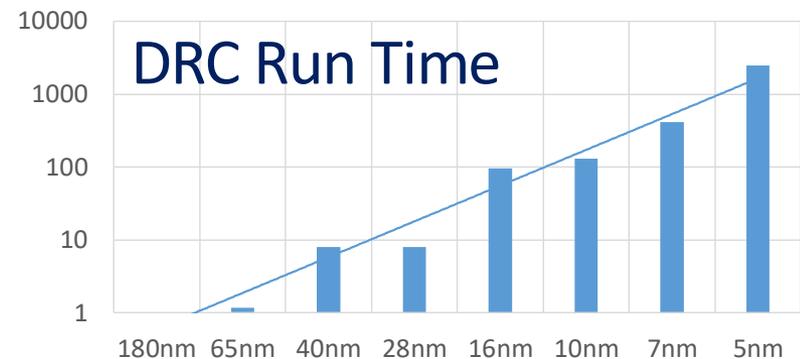
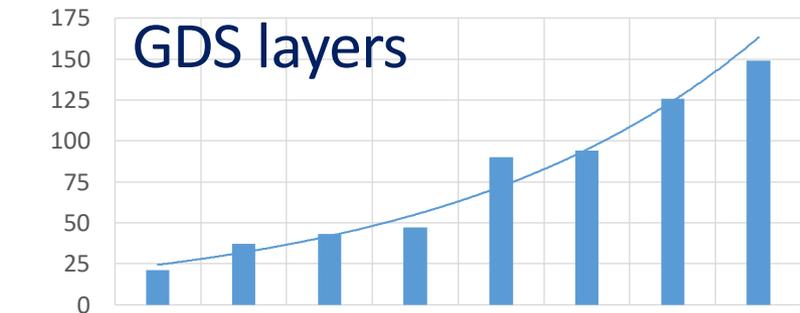
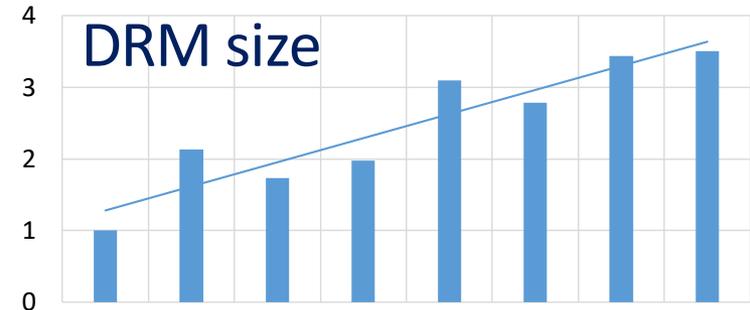
Analog scaling to 5nm

- Analog noise relates to kT/C , so area should scale with capacitance area
- It does! Analog scales, but less than digital
- From 180nm to 5nm:
 - Digital scaling is $\sim 800:1$
 - Analog scaling is $\sim 8:1$



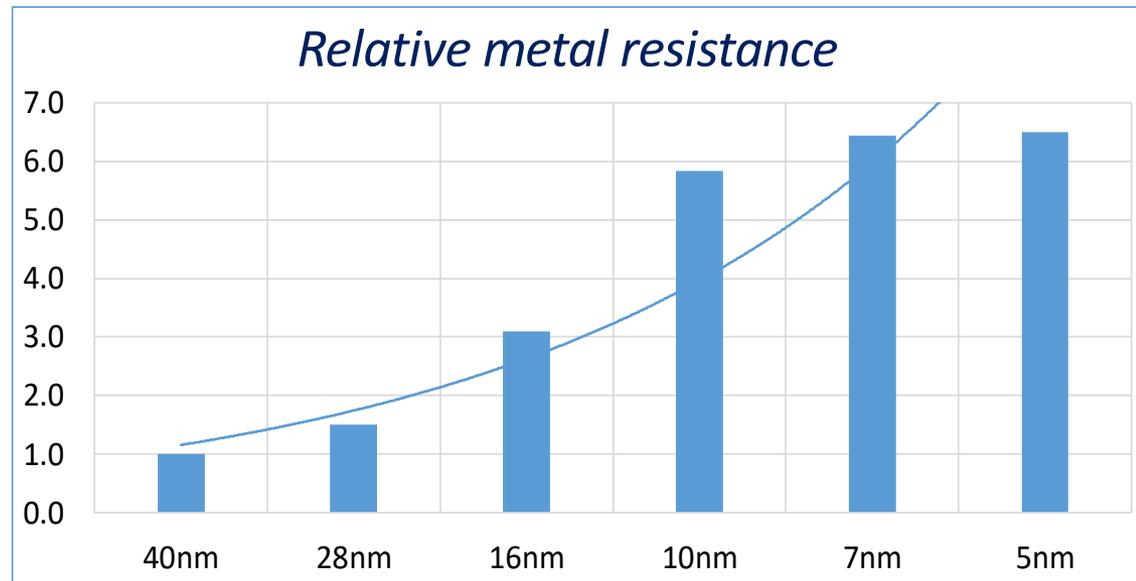
5nm Process Complexity

- DRM size
 - From 180nm to FinFET, the # DRM pages increased 3.5x
- GDS layer count
 - Increased 7x
- Relative DRC Run Time
 - More complex rules, more fill geometries
 - Run times compared to 28nm:
 - 16nm FinFET are ~10x longer
 - 7nm FinFET are ~50x longer
 - 5nm FinFET are ~300x longer



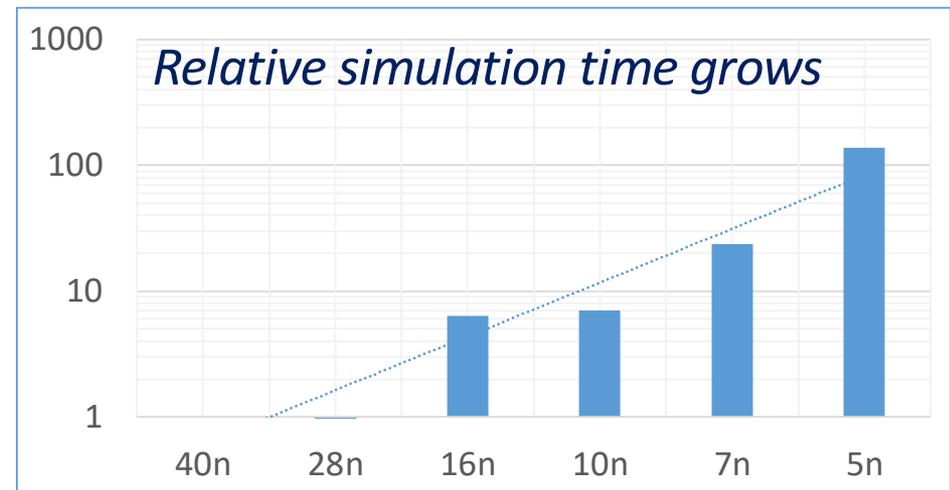
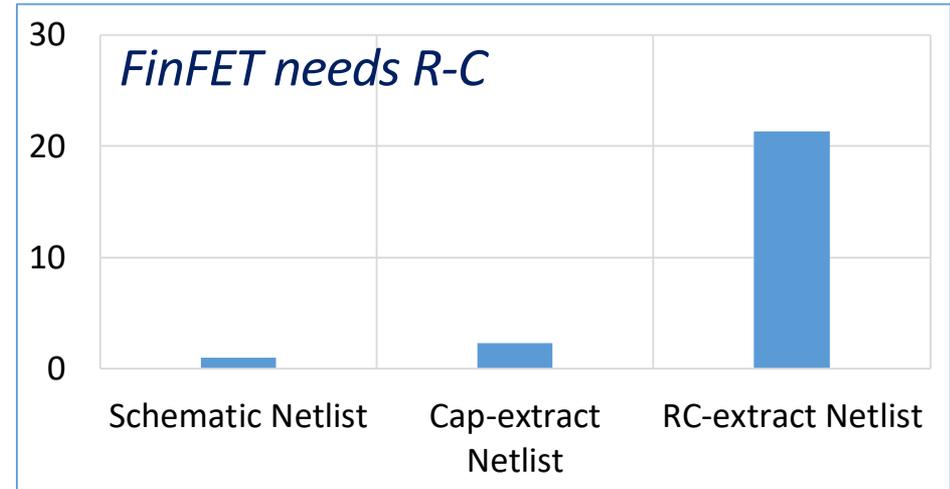
Wire resistance challenge

- Interconnect resistance is climbing quickly!
- Extraction and post extract simulations are becoming more important
- From 40nm to 5nm/7nm, wire resistance (Ω/sq) has risen $\sim 6.5x$
- Designs are increasingly difficult to verify due to the need for simulation of distributed RC parasitics



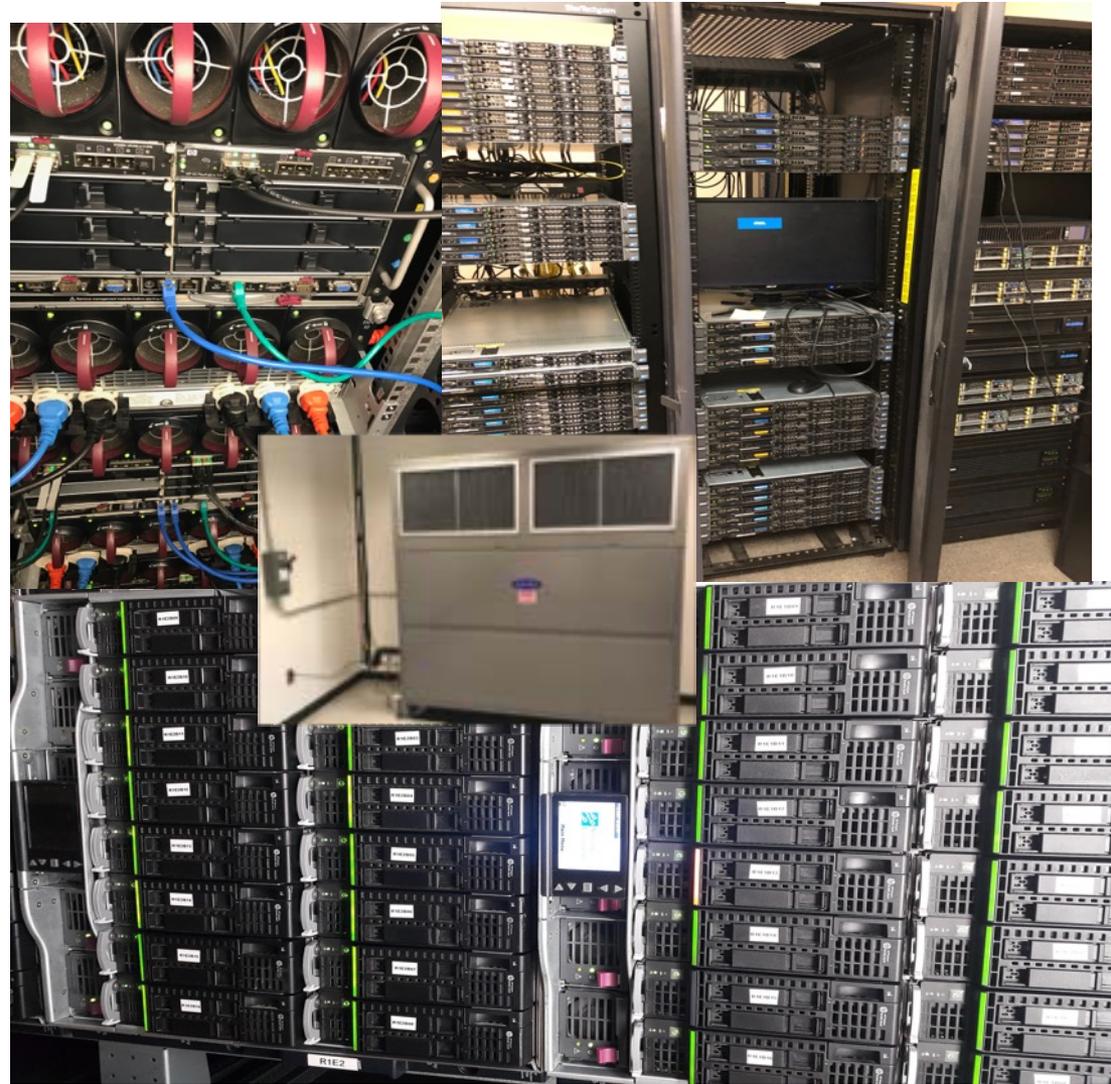
5nm Simulation Time

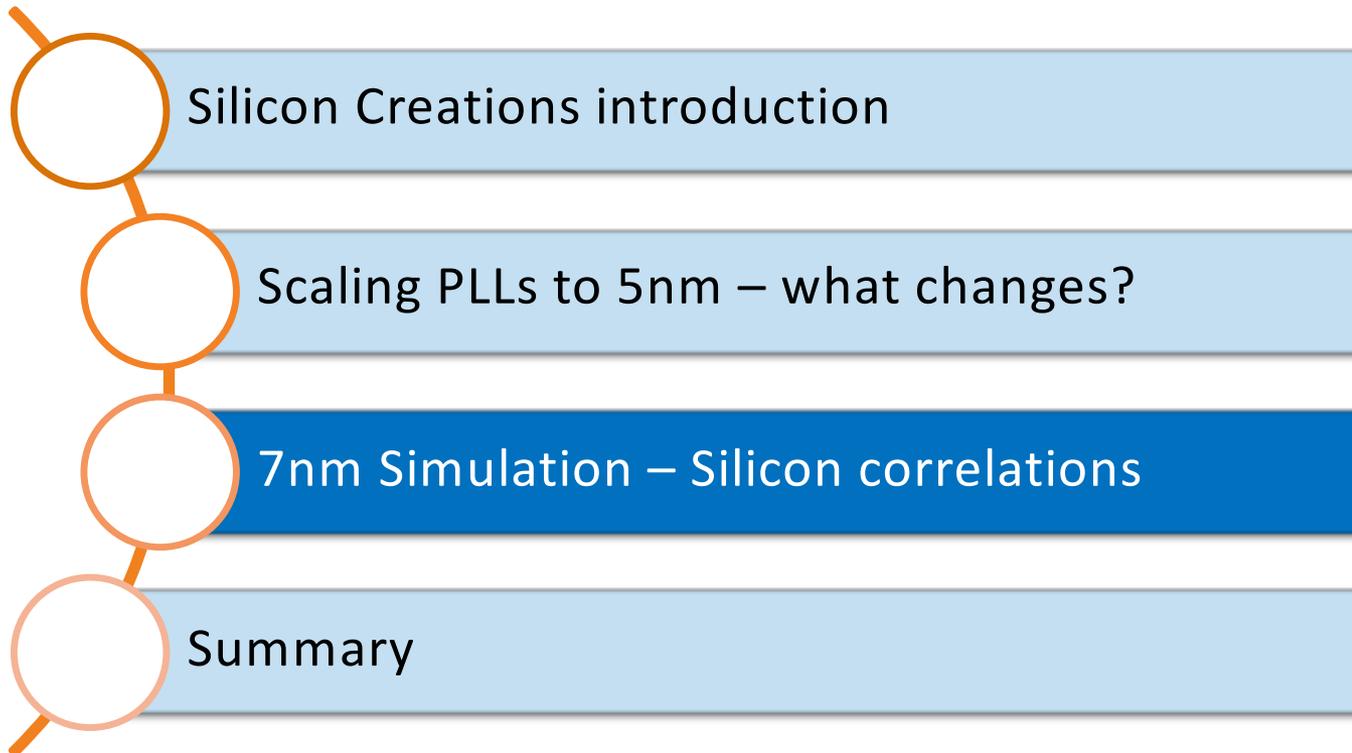
- Schematic sims are out, distributed C-C and R-C extracted simulations are needed
- Translates to Higher development costs:
 - Longer development cycles
 - Need parallel simulation and more CPU's
 - Need more EDA licenses



5nm Computing Solution

- Distributed computing farm
 - 2200+ CPU cores
 - 15TB+ RAM
- 1200 Simulation licenses
 - 200+ 16-core extracted sims
 - 300+ 4-core extracted sims
- Dedicated Calibre machines
 - Intel i9-7980XE 4.8GHz
 - World's fastest 18-core machine
 - CPU de-capped, water-cooled
 - 4x16GB DDR4 RAM
- Carrier 15 Ton Cooling Units
 - >50kW Capacity
- 140 kW at full capacity!

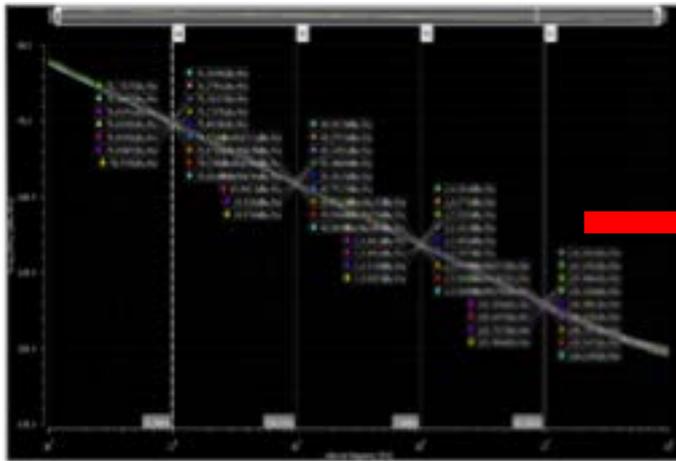




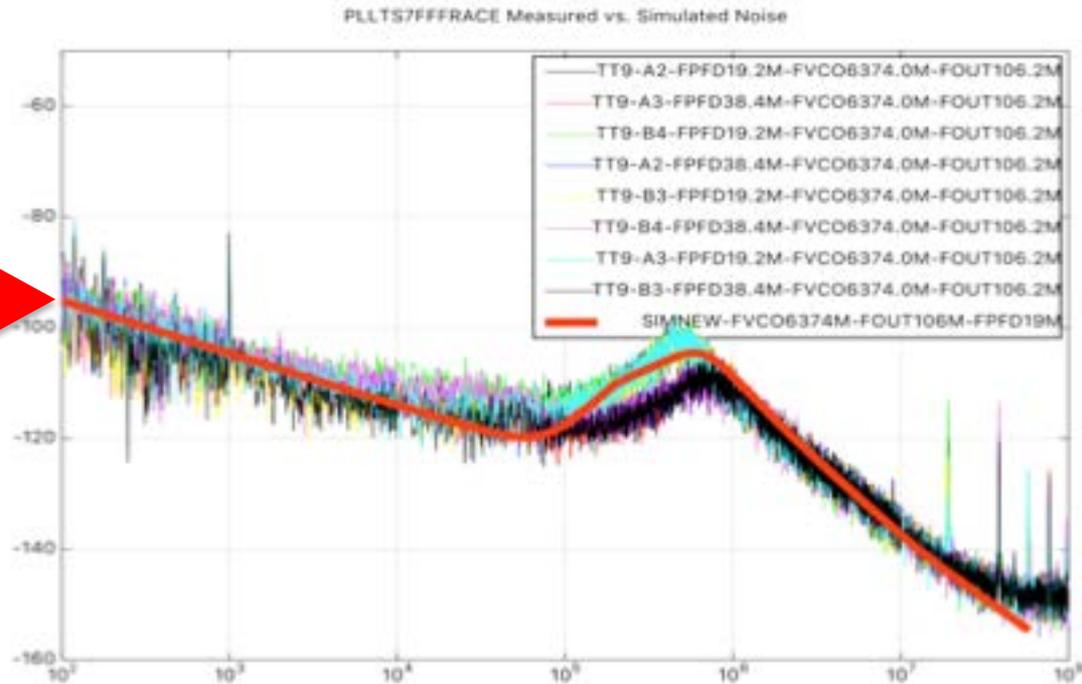
Simulation = 7nm Silicon



Excellent correspondence between Mentor AFS derived phase noise and measured performance



AFS PSS + Pnoise
(VCO, Charge pump)



7nm IoT PLL Power



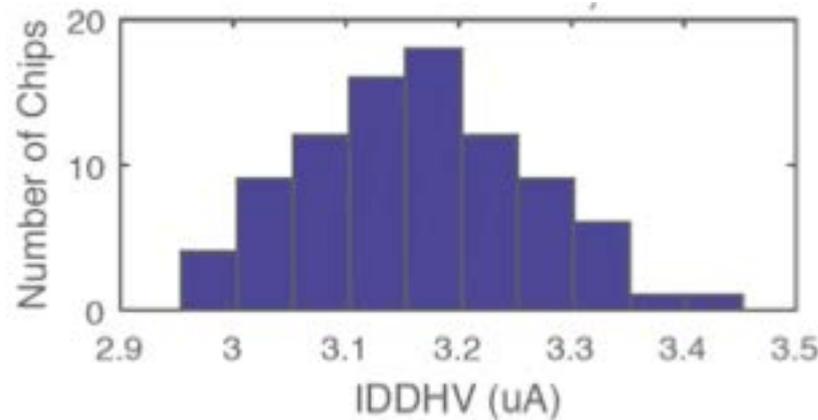
- Simulation

- Mean=3.02uA
- Stddev=1.5%

- Measurement

- Mean=3.15uA
- Stddev=1.6%

Measured Current Distribution



- Silicon Creations provides PLLs, interfaces such as LVDS and SerDes to 25Gbps
- Market leader in PLLs – already in production in 7nm, well underway in 5nm
- Designing in FinFET brings many challenges including simulation complexity and runtime; need to pay close attention to parasitics, proximity and matching, and balance accuracy and design time
- 5nm is significantly more complex than 16nm/12nm, but no new techniques are needed; our PLL circuit topology has worked from 180nm to 5nm